

## SIPMOS Chip-Produkte/SIPMOS Die Products

### SIPMOS Power Transistor Dice

$V_{DS(max)}$	$R_{DS(on)max}$	Die type	Recommended source bond wire diameter <sup>1)</sup> $\mu m$	Die topology	Page
V	$\Omega$				
-200	1.500	SIPC08P20	250	<sup>2)</sup>	-
-100	0.600	SIPC08P10	250	<sup>2)</sup>	-
50	0.030	SIPC20AN05	500	PF	1184
	0.035	SIPC20AN05L	500	PF	1184
	0.055	SIPC14AN05	500	PD	1184
	0.055	SIPC14AN05L	500	PD	1184
	0.070	SIPC08AN05	500	PB	1184
	0.070	SIPC08AN05L	500	PB	1184
	0.100	SIPC06AN05	350	PA	1184
	0.100	SIPC06AN05L	350	PA	1184
60	0.055	SIPC14AN06	500	PD	1184
	0.070	SIPC08AN06	500	PB	1184
	0.120	SIPC06AN06	350	PA	1184
	0.150	SIPC05AN06L	250	<sup>2)</sup>	-
	0.150	SIPC05AN06	250	<sup>2)</sup>	-
100	0.055	SIPC20AN10	500	PF	1184
	0.085	SIPC14AN10	350	PD	1184
	0.100	SIPC14AN10L	350	PD	1184
	0.250	SIPC08AN10	250	PB	1184
	0.250	SIPC08AN10L	250	PB	1184
200	0.130	SIPC20AN20	500	PF	1184
	0.200	SIPC14AN20	350	PD	1184
	0.600	SIPC08AN20	250	PB	1184
	0.600	SIPC08AN20L	250	PB	1184
400	1.000	SIPC14AN40	250	PD	1184
	1.000	SIPC14AN40F	250	PE	1184
	2.500	SIPC08AN40	250	PB	1184
500	1.500	SIPC14AN50	250	PD	1184
	2.000	SIPC14AN50F	250	PE	1184
	2.000	SIPC10AN50	250	PC	1184
	4.000	SIPC08AN50	250	PB	1184
600	2.000	SIPC14AN60	250	PD	1184
	3.000	SIPC10AN60	250	PC	1184
	4.000	SIPC08AN60	250	PB	1184
800	4.000	SIPC16AN80	250	<sup>2)</sup>	-
	8.000	SIPC08AN80	250	PB	1184
1000	8.000	SIPC14AN100	250	PD	1184

P  $\Delta$  Power

<sup>1)</sup> The recommended gate bond wire diameter is 125  $\mu m$ .

<sup>2)</sup> On request.